

ISC Silicon NPN Power Transistor

2SC3480

DESCRIPTION

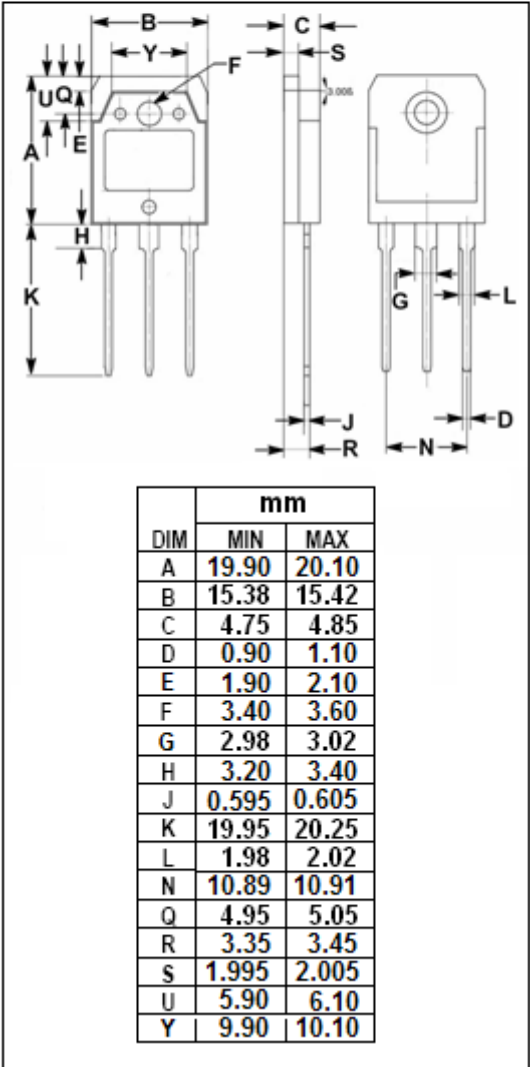
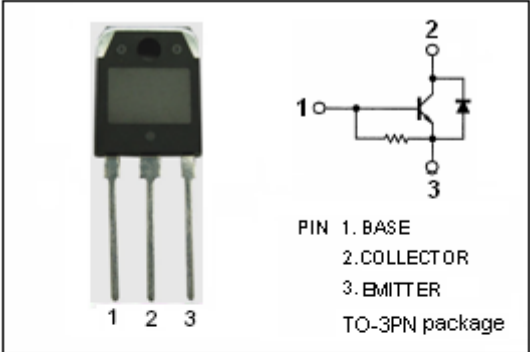
- High Breakdown Voltage-
: $V_{CBO}=1500V$ (Min)
- High Switching Speed
- High Reliability
- Built-in Damper Diode

APPLICATIONS

- Designed for high definition CRT display horizontal deflection output applications.

ABSOLUTE MAXIMUM RATINGS($T_a=25^{\circ}C$)

SYMBOL	PARAMETER	VALUE	UNIT
V_{CBO}	Collector-Base Voltage	1500	V
V_{CEO}	Collector-Emitter Voltage	800	V
V_{EBO}	Emitter-Base Voltage	7	V
I_C	Collector Current- Continuous	3.5	A
P_C	Collector Power Dissipation @ $T_C=25^{\circ}C$	80	W
T_J	Junction Temperature	150	$^{\circ}C$
T_{stg}	Storage Temperature Range	-55~150	$^{\circ}C$



ISC Silicon NPN Power Transistor**2SC3480****ELECTRICAL CHARACTERISTICS****T_C=25°C unless otherwise specified**

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT
V _{(BR)CEO}	Collector-Emitter Breakdown Voltage	I _C = 5mA; R _{BE} = ∞	800			V
V _{(BR)CBO}	Collector-Base Breakdown Voltage	I _C = 5mA; I _E = 0	1500			V
V _{(BR)EBO}	Emitter-Base Breakdown Voltage	I _E = 200mA; I _C = 0	7			V
V _{CE(sat)}	Collector-Emitter Saturation Voltage	I _C = 2.5A; I _B = 0.8A			8.0	V
V _{BE(sat)}	Base-Emitter Saturation Voltage	I _C = 2.5A; I _B = 0.8A			1.5	V
I _{CBO}	Collector Cutoff Current	V _{CB} = 800V; I _E = 0			10	μ A
I _{EBO}	Emitter Cutoff Current	V _{EB} = 4V; I _C = 0	40		130	mA
h _{FE}	DC Current Gain	I _C = 0.5A; V _{CE} = 5V	8			
V _{ECF}	C-E Diode Forward Voltage	I _F = 2.5A			2.0	V
f _T	Current-Gain—Bandwidth Product	I _C = 0.5A; V _{CE} = 10V		3		MHz